

Configurable Multiple-Function Gate

Check for Samples: SN74LVC1G58

FEATURES

- Available in the Texas Instruments NanoFree[™] Package
- Supports 5-V V_{CC} Operation
- Inputs Accept Voltages to 5.5 V
- Supports Down Translation to V_{CC}
- Max t_{pd} of 6.3 ns at 3.3 V
- Low Power Consumption, 10-μA Max I_{CC}
- ±24-mA Output Drive at 3.3 V
- I_{off} Supports Live Insertion, Partial-Power-Down Mode, and Back-Drive Protection
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Protection Exceeds JESD 22
 - 2000-V Human-Body Model (A114-A)
 - 200-V Machine Model (A115-A)
 - 1000-V Charged-Device Model (C101)

DESCRIPTION

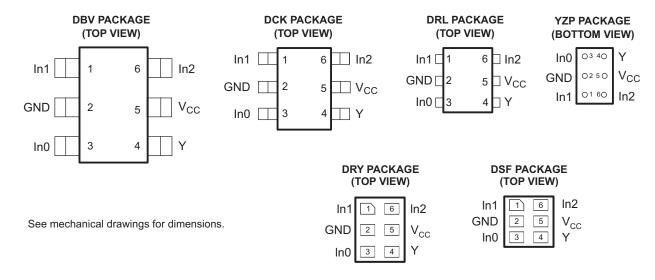
This configurable multiple-function gate is designed for 1.65-V to 5.5-V $V_{\rm CC}$ operation.

The SN74LVC1G58 device features configurable multiple functions. The output state is determined by eight patterns of 3-bit input. The user can choose the logic functions AND, OR, NAND, NOR, XOR, inverter, and noninverter. All inputs can be connected to V_{CC} or GND.

This device functions as an independent gate, but because of Schmitt action, it may have different input threshold levels for positive-going (V_{T+}) and negative-going (V_{T-}) signals.

NanoFree $^{\text{TM}}$ package technology is a major breakthrough in IC packaging concepts, using the die as the package.

This device is fully specified for partial-power-down applications using $I_{\rm off}$. The $I_{\rm off}$ circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.



W

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



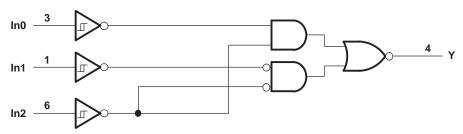


These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

Function Table

	INPUTS	OUTPUT						
ln2	ln1	In0	Y					
L	L	L	L					
L	L	Н	Н					
L	Н	L	L					
L	Н	Н	Н					
Н	L	L	Н					
Н	L	Н	Н					
Н	Н	L	L					
Н	Н	Н	L					

Logic Diagram (Positive Logic)



Function Selection Table

FIGURE NO.						
Figure 2, Figure 3						
Figure 1						
Figure 4						
Figure 4						
Figure 1						
Figure 2, Figure 3						
Figure 5						



Logic Configurations

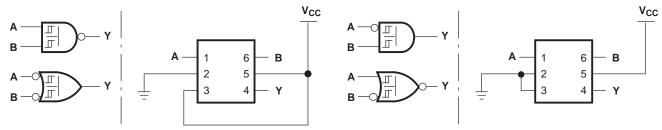


Figure 1. 2-Input NAND Gate

Figure 2. 2-Input AND Gate With Inverted A Input

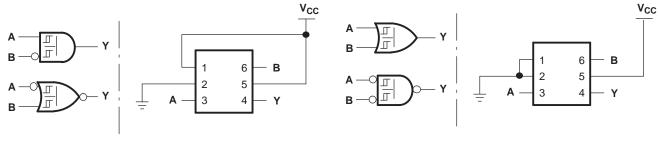


Figure 3. 2-Input AND Gate With Inverted B Input

Figure 4. 2-Input OR Gate

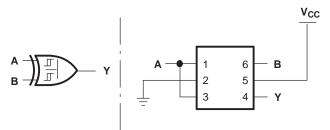


Figure 5. 2-Input XOR Gate

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Absolute Maximum Ratings(1)

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V_{CC}	Supply voltage range		-0.5	6.5	V
VI	Input voltage range (2)		-0.5	6.5	V
Vo	Voltage range applied to any output in the high-im	npedance or power-off state (2)	-0.5	6.5	V
Vo	Voltage range applied to any output in the high or	low state (2)(3)	-0.5	V _{CC} + 0.5	V
I _{IK}	Input clamp current	V _I < 0		-50	mA
I _{OK}	Output clamp current	V _O < 0		-50	mA
Io	Continuous output current			±50	mA
	Continuous current through V _{CC} or GND			±100	mA
		DBV package		165	
^	D1(4)	DCK package		259	0000
θ_{JA}	Package thermal impedance (4)	DRL package		142	°C/W
		YZP package		123	
T _{stg}	Storage temperature range		-65	150	°C

⁽¹⁾ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

Recommended Operating Conditions⁽¹⁾

			MIN	MAX	UNIT
.,	Operating	Operating	1.65	5.5	V
V _{CC}	Supply voltage	Data retention only	1.5		V
VI	Input voltage		0	5.5	V
Vo	Output voltage		0	V _{CC}	V
		V _{CC} = 1.65 V		-4	
	High-level output current	V _{CC} = 2.3 V		-8	
I_{OH}		V 2V		-16	mA
		V _{CC} = 3 V		-24	
		V _{CC} = 4.5 V		-32	
		V _{CC} = 1.65 V		4	
		V _{CC} = 2.3 V		8	
I_{OL}	Low-level output current	V 2V		16	mA
		V _{CC} = 3 V		24	
		V _{CC} = 4.5 V		32	
T _A	Operating free-air temperature		-40	125	°C

 All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.

Product Folder Links: SN74LVC1G58

⁽²⁾ The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.

⁽³⁾ The value of V_{CC} is provided in the recommended operating conditions table.

⁽⁴⁾ The package thermal impedance is calculated in accordance with JESD 51-7.



Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

DADAMETER	TEST COMPLETIONS	,,	-40°(C to 85°C	-40°C	to 125°C	LINIT
PARAMETER	TEST CONDITIONS	V _{cc}	MIN	TYP ⁽¹⁾ MAX	MIN	TYP ⁽¹⁾ MAX	UNIT
		1.65 V	0.79	1.16	0.79	1.16	
V _{T+}		2.3 V	1.11	1.56	1.11	1.56	
Positive-going input		3 V	1.5	1.87	1.5	1.87	V
threshold voltage		4.5 V	2.16	2.74	2.16	2.74	
		5.5 V	2.61	3.33	2.61	3.33	
		1.65 V	0.35	0.62	0.35	0.62	
V _T		2.3 V	0.58	0.87	0.58	0.87	
Negative-going input		3 V	0.84	1.19	0.84	1.19	V
threshold voltage		4.5 V	1.41	1.9	1.41	1.9	
		5.5 V	1.87	2.29	1.87	2.29	
		1.65 V	0.3	0.62	0.3	0.62	
		2.3 V	0.4	0.8	0.4	0.8	
ΔV_T Hysteresis ($V_{T+} - V_{T-}$)		3 V	0.53	0.87	0.53	0.87	V
11y3tc1c3i3 (V + V _)		4.5 V	0.71	1.04	0.71	1.04	
		5.5 V	0.71	1.11	0.71	1.11	
	I _{OH} = -100 μA	1.65 V to 5.5 V	V _{CC} - 0.1		V _{CC} - 0.1		
	I _{OH} = -4 mA	1.65 V	1.2		1.2		
W	$I_{OH} = -8 \text{ mA}$	2.3 V	1.9		1.9		V
V _{OH}	I _{OH} = -16 mA	2.1/	2.4		2.4		V
	$I_{OH} = -24 \text{ mA}$	3 V	2.3		2.3		
	I _{OH} = -32 mA	4.5 V	3.8		3.8		
	I _{OL} = 100 μA	1.65 V to 5.5 V		0.1		0.1	
	I _{OL} = 4 mA	1.65 V		0.45		0.45	
V	I _{OL} = 8 mA	2.3 V		0.3		0.3	V
V_{OL}	I _{OL} = 16 mA	3 V		0.4		0.45	V
	I _{OL} = 24 mA	3 V		0.55		0.55	
	I _{OL} = 32 mA	4.5 V		0.55		0.58	
I _I	V _I = 5.5 V or GND	0 to 5.5 V		±1		±1	μΑ
l _{off}	V_I or $V_O = 5.5 \text{ V}$	0		±10		±10	μΑ
I _{cc}	$V_I = 5.5 \text{ V or GND}, I_O = 0$	1.65 V to 5.5 V		10		10	μΑ
ΔI _{CC}	One input at V _{CC} – 0.6 V, Other inputs at V _{CC} or GND	3 V to 5.5 V		500		500	μА
C _i	$V_I = V_{CC}$ or GND	3.3 V		3.5			pF

⁽¹⁾ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.



Switching Characteristics

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 6)

							/C1G58 to 85°C										
PARAMETER	FROM (INPUT)	TO (OUTPUT)		V _{CC} = 1.8 V ± 0.15 V									V _{CC} = ± 0.		V _{CC} =		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX							
t _{pd}	Any In	Υ	3.2	14.4	2	8.3	1.5	6.3	1.1	5.1	ns						

Switching Characteristics

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 6)

	J	3 (/C1G58 o 125°C													
PARAMETER	FROM (INPUT)																	V _{CC} = ± 0.		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX										
t _{pd}	Any In	Υ	3.2	16.4	2	9.3	1.5	7.3	1.1	6.1	ns									

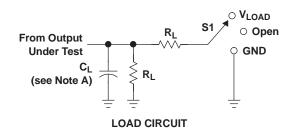
Operating Characteristics

 $T_A = 25^{\circ}C$

PARAMETER		TEST	V _{CC} = 1.8 V	V _{CC} = 2.5 V	V _{CC} = 3.3 V	V _{CC} = 5 V	UNIT
		CONDITIONS	TYP	TYP	TYP	TYP	J
C_{pd}	Power dissipation capacitance	f = 10 MHz	22	22	23	24	pF



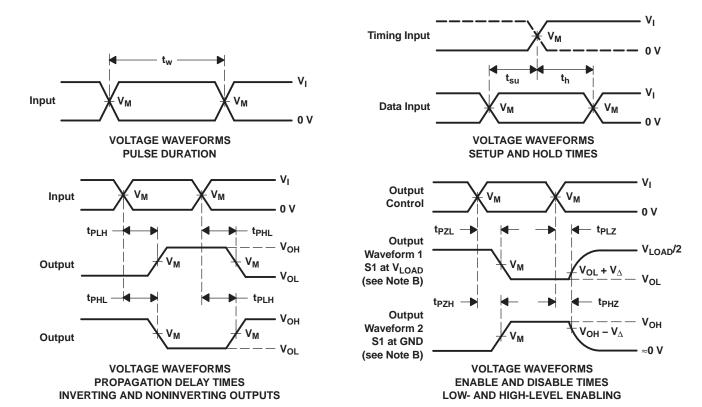
Parameter Measurement Information



TEST	S1
t _{PLH} /t _{PHL}	Open
t _{PLZ} /t _{PZL}	V _{LOAD}
t _{PHZ} /t _{PZH}	GND

V	IN

.,	INI	PUTS	.,	.,	_	-	.,
V _{CC}	VI	t _r /t _f	V _M	V _{LOAD}	CL	R _L	V_{Δ}
1.8 V ± 0.15 V	V _{CC}	≤2 ns	V _{CC} /2	2×V _{CC}	30 pF	1 k Ω	0.15 V
2.5 V \pm 0.2 V	V _{CC}	≤2 ns	V _{CC} /2	2×V _{CC}	30 pF	500 Ω	0.15 V
3.3 V \pm 0.3 V	3 V	≤2.5 ns	1.5 V	6 V	50 pF	500 Ω	0.3 V
5 V \pm 0.5 V	V _{CC}	≤2.5 ns	V _{CC} /2	2×V _{CC}	50 pF	500 Ω	0.3 V



NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_0 = 50 Ω .
- D. The outputs are measured one at a time, with one transition per measurement.
- E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
- F. t_{PZL} and t_{PZH} are the same as t_{en}.
- G. t_{PLH} and t_{PHL} are the same as t_{pd}.
- H. All parameters and waveforms are not applicable to all devices.

Figure 6. Load Circuit and Voltage Waveforms

SCES415N - NOVEMBER 2002 - REVISED DECEMBER 2013



REVISION HISTORY

Changes from Revision K (January 2007) to Revision L						
Added additional package options in the Ordering Information table	1					
Added DRY and DSF packages to datasheet	1					
Changes from Revision L (October 2011) to Revision M	Page					
Removed Ordering Information table, package updates now included in Package Orderi	ng Addendum 1					
Changes from Revision M (April 2013) to Revision N	Page					
Updated document to new TI data sheet format.	1					
Updated Features.	1					
Added ESD warning.	2					
Updated operating temperature range.	4					

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PACKAGING INFORMATION

Orderable part number	Status	Material type	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking (6)
SN74LVC1G58DBVR	Active	Production	SOT-23 (DBV) 6	3000 LARGE T&R	Yes	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	(C585, C58R)
SN74LVC1G58DBVR.B	Active	Production	SOT-23 (DBV) 6	3000 LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	(C585, C58R)
SN74LVC1G58DCKR	Active	Production	SC70 (DCK) 6	3000 LARGE T&R	Yes	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	(CP5, CPF, CPK, CP R)
SN74LVC1G58DCKR.B	Active	Production	SC70 (DCK) 6	3000 LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	(CP5, CPF, CPK, CP R)
SN74LVC1G58DCKRE4	Active	Production	SC70 (DCK) 6	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	CPF
SN74LVC1G58DCKRG4	Active	Production	SC70 (DCK) 6	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	CPF
SN74LVC1G58DCKRG4.B	Active	Production	SC70 (DCK) 6	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	CPF
SN74LVC1G58DRLR	Active	Production	SOT-5X3 (DRL) 6	4000 LARGE T&R	Yes	NIPDAU NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	(1K3, CP7, CPR)
SN74LVC1G58DRLR.B	Active	Production	SOT-5X3 (DRL) 6	4000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	(1K3, CP7, CPR)
SN74LVC1G58DRLRG4	Active	Production	SOT-5X3 (DRL) 6	4000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	1K3
SN74LVC1G58DRLRG4.B	Active	Production	SOT-5X3 (DRL) 6	4000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	1K3
SN74LVC1G58DRY2	Active	Production	SON (DRY) 6	5000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	СР
SN74LVC1G58DRY2.B	Active	Production	SON (DRY) 6	5000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	СР
SN74LVC1G58DRYR	Active	Production	SON (DRY) 6	5000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	СР
SN74LVC1G58DRYR.B	Active	Production	SON (DRY) 6	5000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	СР
SN74LVC1G58DRYRG4	Active	Production	SON (DRY) 6	5000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	СР
SN74LVC1G58DRYRG4.B	Active	Production	SON (DRY) 6	5000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	СР
SN74LVC1G58DSF2	Active	Production	SON (DSF) 6	5000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	СР
SN74LVC1G58DSF2.B	Active	Production	SON (DSF) 6	5000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	СР
SN74LVC1G58DSFR	Active	Production	SON (DSF) 6	5000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	CP
SN74LVC1G58DSFR.B	Active	Production	SON (DSF) 6	5000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	CP
SN74LVC1G58YZPR	Active	Production	DSBGA (YZP) 6	3000 LARGE T&R	Yes	SNAGCU	Level-1-260C-UNLIM	-40 to 85	CPN
SN74LVC1G58YZPR.B	Active	Production	DSBGA (YZP) 6	3000 LARGE T&R	Yes	SNAGCU	Level-1-260C-UNLIM	-40 to 85	CPN

⁽¹⁾ Status: For more details on status, see our product life cycle.

⁽²⁾ Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

PACKAGE OPTION ADDENDUM

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- (3) RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.
- (4) Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.
- (5) MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.
- (6) Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.



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TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74LVC1G58DBVR	SOT-23	DBV	6	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
SN74LVC1G58DCKR	SC70	DCK	6	3000	180.0	8.4	2.3	2.5	1.2	4.0	8.0	Q3
SN74LVC1G58DCKRG4	SC70	DCK	6	3000	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
SN74LVC1G58DRLR	SOT-5X3	DRL	6	4000	180.0	8.4	2.0	1.8	0.75	4.0	8.0	Q3
SN74LVC1G58DRLRG4	SOT-5X3	DRL	6	4000	180.0	8.4	2.0	1.8	0.75	4.0	8.0	Q3
SN74LVC1G58DRY2	SON	DRY	6	5000	180.0	9.5	1.6	1.15	0.75	4.0	8.0	Q3
SN74LVC1G58DRYR	SON	DRY	6	5000	180.0	9.5	1.15	1.6	0.75	4.0	8.0	Q1
SN74LVC1G58DRYRG4	SON	DRY	6	5000	180.0	9.5	1.15	1.6	0.75	4.0	8.0	Q1
SN74LVC1G58DSF2	SON	DSF	6	5000	180.0	9.5	1.16	1.16	0.5	4.0	8.0	Q3
SN74LVC1G58DSFR	SON	DSF	6	5000	180.0	9.5	1.16	1.16	0.5	4.0	8.0	Q2
SN74LVC1G58YZPR	DSBGA	YZP	6	3000	178.0	9.2	1.02	1.52	0.63	4.0	8.0	Q1



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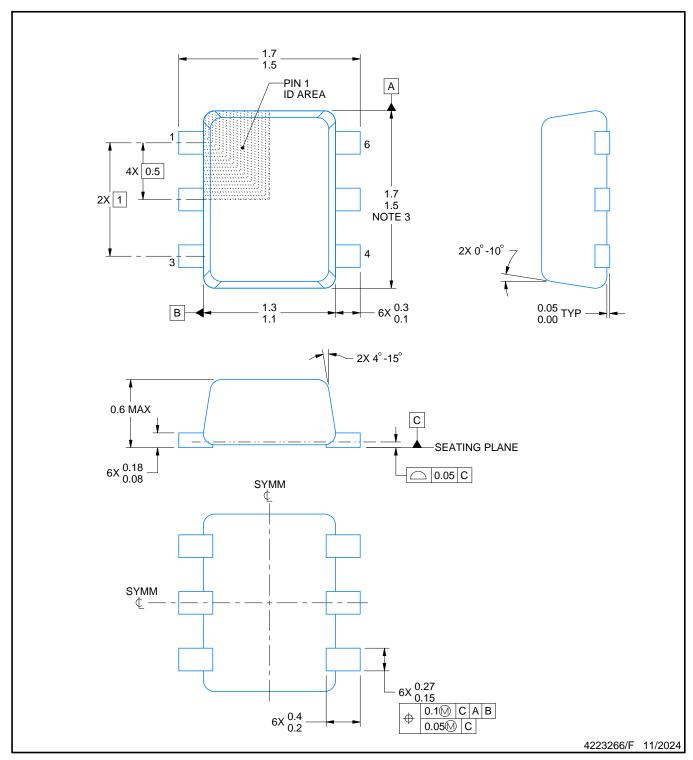


*All dimensions are nominal

All difficultions are norminal								
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)	
SN74LVC1G58DBVR	SOT-23	DBV	6	3000	210.0	185.0	35.0	
SN74LVC1G58DCKR	SC70	DCK	6	3000	210.0	185.0	35.0	
SN74LVC1G58DCKRG4	SC70	DCK	6	3000	180.0	180.0	18.0	
SN74LVC1G58DRLR	SOT-5X3	DRL	6	4000	210.0	185.0	35.0	
SN74LVC1G58DRLRG4	SOT-5X3	DRL	6	4000	210.0	185.0	35.0	
SN74LVC1G58DRY2	SON	DRY	6	5000	184.0	184.0	19.0	
SN74LVC1G58DRYR	SON	DRY	6	5000	184.0	184.0	19.0	
SN74LVC1G58DRYRG4	SON	DRY	6	5000	184.0	184.0	19.0	
SN74LVC1G58DSF2	SON	DSF	6	5000	184.0	184.0	19.0	
SN74LVC1G58DSFR	SON	DSF	6	5000	184.0	184.0	19.0	
SN74LVC1G58YZPR	DSBGA	YZP	6	3000	220.0	220.0	35.0	



PLASTIC SMALL OUTLINE



NOTES:

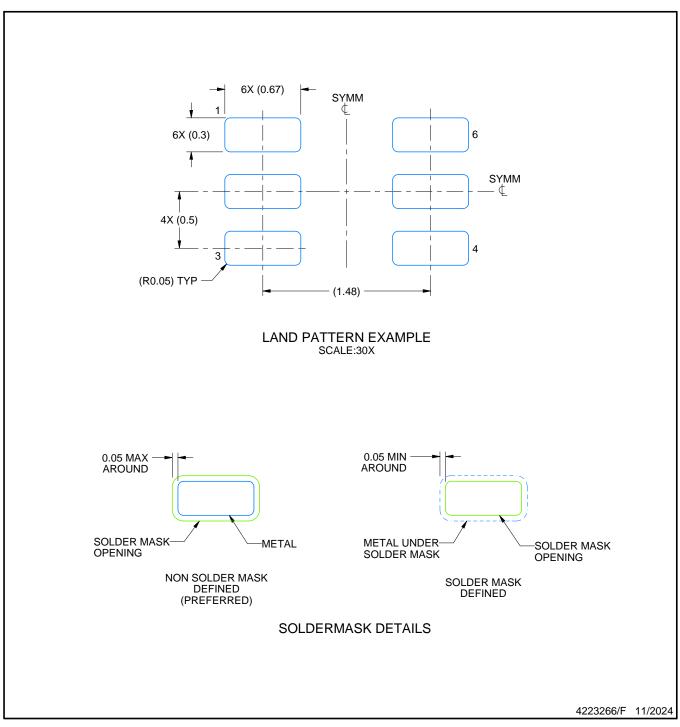
- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
 4. Reference JEDEC registration MO-293 Variation UAAD



PLASTIC SMALL OUTLINE

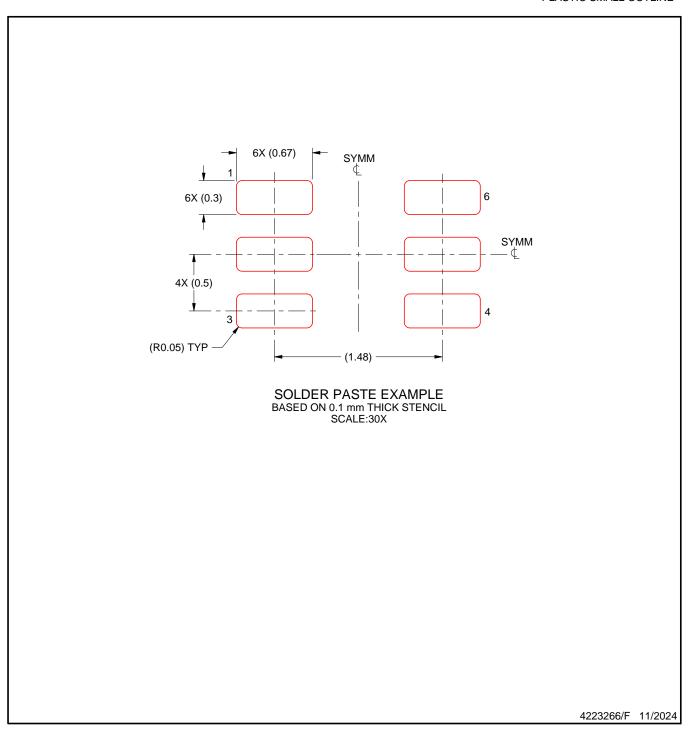


NOTES: (continued)

- 5. Publication IPC-7351 may have alternate designs.
- 6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.7. Land pattern design aligns to IPC-610, Bottom Termination Component (BTC) solder joint inspection criteria.



PLASTIC SMALL OUTLINE



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.







NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.25 per side.

- 4. Leads 1,2,3 may be wider than leads 4,5,6 for package orientation.
- 5. Refernce JEDEC MO-178.





NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





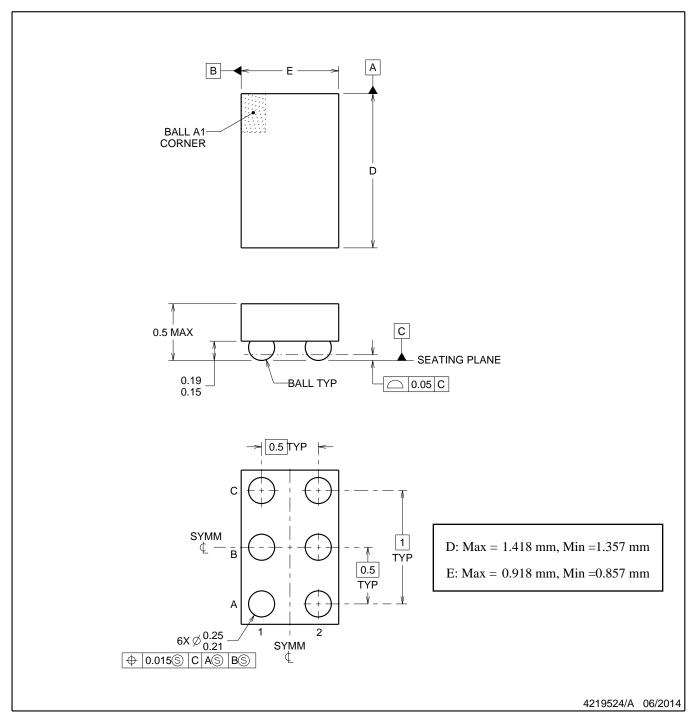
NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.





DIE SIZE BALL GRID ARRAY



NOTES:

NanoFree Is a trademark of Texas Instruments.

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.
- 3. NanoFree[™] package configuration.



DIE SIZE BALL GRID ARRAY



NOTES: (continued)

4. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SBVA017 (www.ti.com/lit/sbva017).



DIE SIZE BALL GRID ARRAY



NOTES: (continued)

5. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.







NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.

 4. Falls within JEDEC MO-203 variation AB.





NOTES: (continued)

5. Publication IPC-7351 may have alternate designs.

6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





NOTES: (continued)

- 7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 8. Board assembly site may have different recommendations for stencil design.





Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.









NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.





NOTES: (continued)

3. For more information, see QFN/SON PCB application report in literature No. SLUA271 (www.ti.com/lit/slua271).





NOTES: (continued)

Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.







NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. Reference JEDEC registration MO-287, variation X2AAF.





NOTES: (continued)

4. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).





4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



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